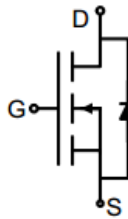


N-Channel Trench MOSFET

Description The G08N02H uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.		 Schematic diagram	
General Features • V_{DS} 20V • I_D (at $V_{GS} = 10V$) 12A • $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 11.3mΩ • $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) < 12.7mΩ • 100% Avalanche Tested • RoHS Compliant		 SOT-223-3L	
Application • Power switch • DC/DC converters			
Device	Package	Marking	Packaging
G08N02H	SOT-223-3L	G08N02	4000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	20	V
Continuous Drain Current	I_D	12	A
Pulsed Drain Current (note1)	I_{DM}	48	A
Gate-Source Voltage	V_{GSS}	± 12	V
Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

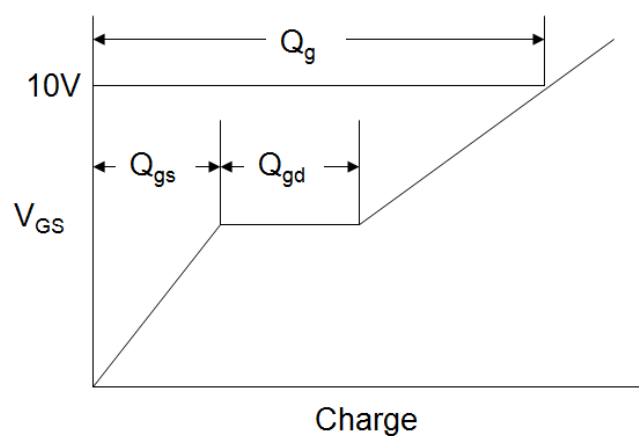
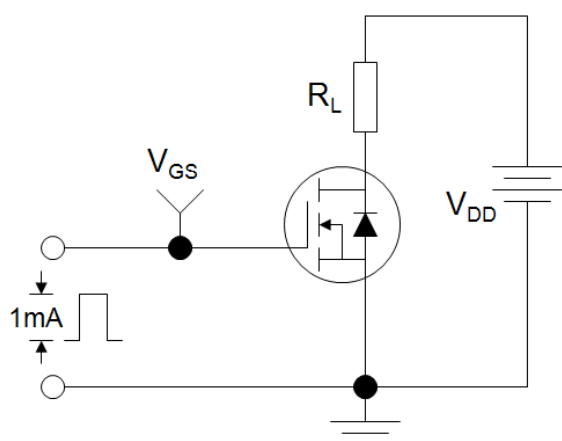
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	61	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±12V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.65	0.9	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 1A	--	8.8	11.3	mΩ
		V _{GS} = 4.5V, I _D = 12A	--	8.9	11.3	
		V _{GS} = 2.5V, I _D = 1A	--	10	12.7	
		V _{GS} = 2.5V, I _D = 12A	--	10.3	12.7	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =10A	--	65	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1.0MHz	--	1255	--	pF
Output Capacitance	C _{oss}		--	220	--	
Reverse Transfer Capacitance	C _{rss}		--	168	--	
Total Gate Charge	Q _g	V _{DD} = 10V, I _D = 10A, V _{GS} = 4.5V	--	12.5	--	nC
Gate-Source Charge	Q _{gs}		--	5.5	--	
Gate-Drain Charge	Q _{gd}		--	6.5	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10V, I _D = 10A, R _G = 3Ω	--	1.1	--	ns
Turn-on Rise Time	t _r		--	2.6	--	
Turn-off Delay Time	t _{d(off)}		--	7	--	
Turn-off Fall Time	t _f		--	7.4	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	2.5	A
Pulsed Diode Forward Current	I _{SM}		--	--	10	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 3A, V _{GS} = 0V	--	--	1.2	V

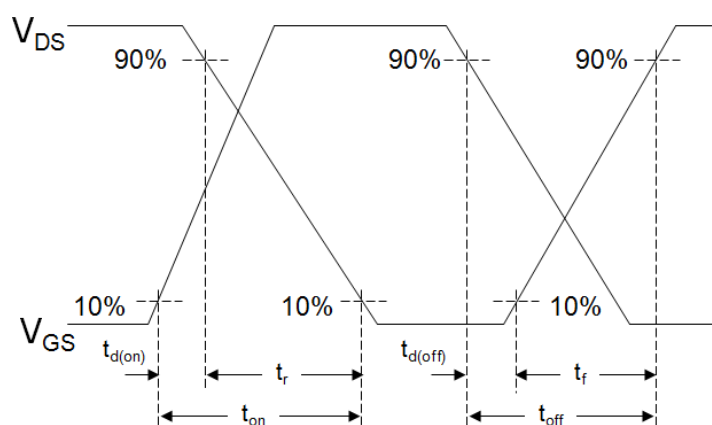
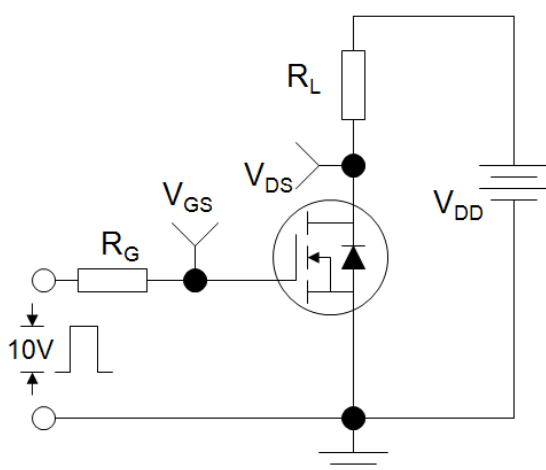
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

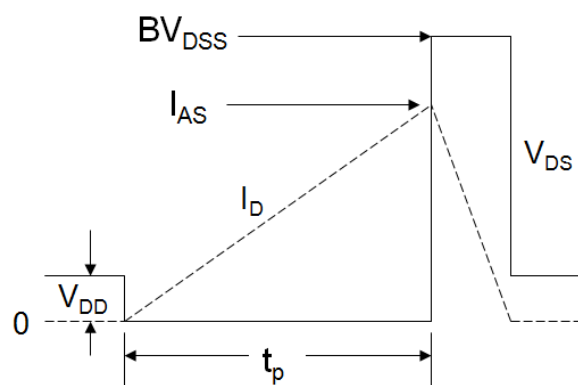
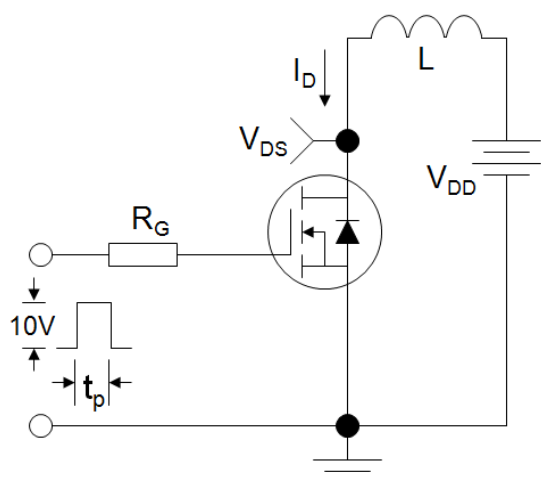
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

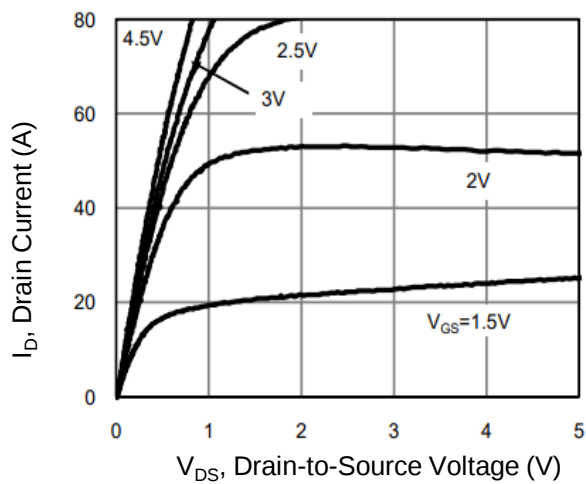


Figure 2. Transfer Characteristics

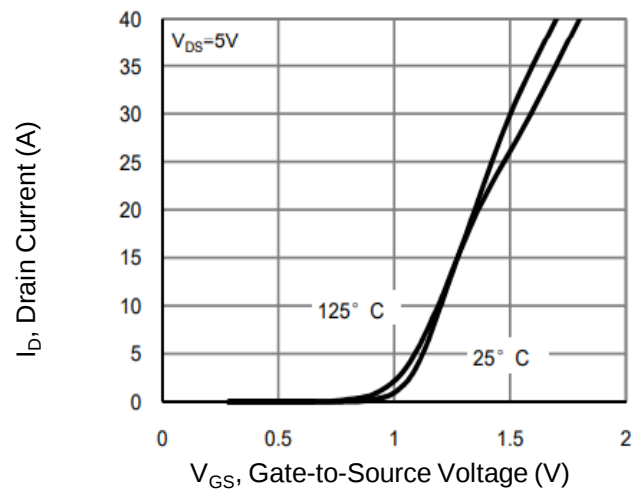


Figure 3. Drain Source On Resistance

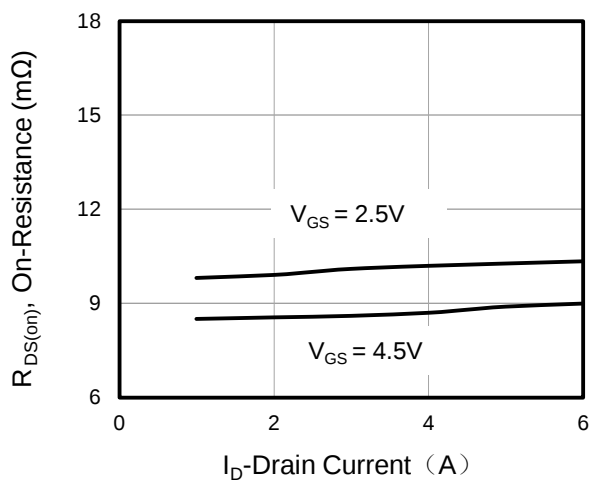


Figure 4. Gate Charge

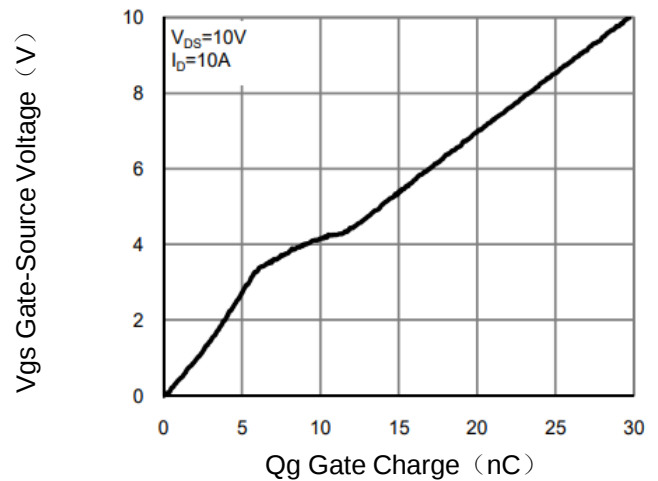


Figure 5. Drain-Source On-Resistance

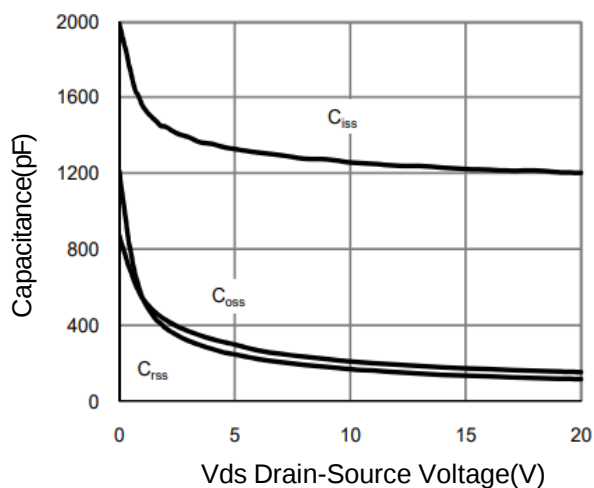
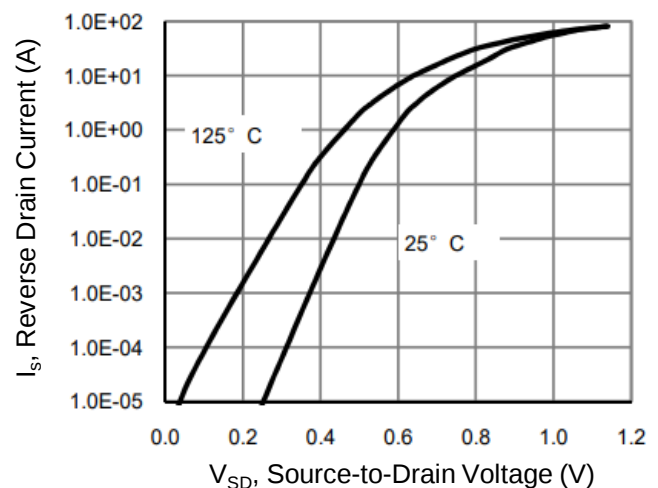


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

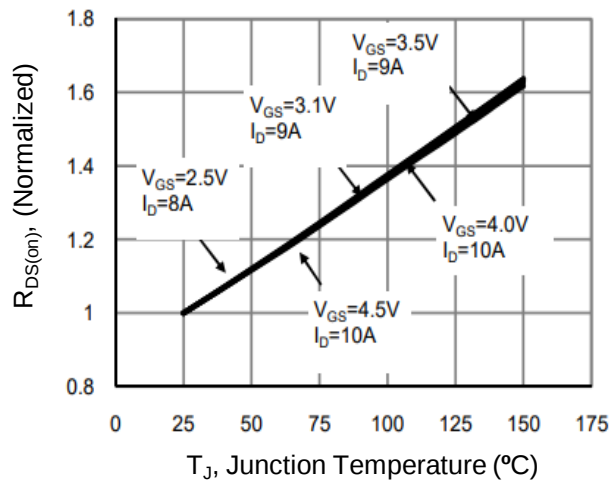


Figure 8. Safe Operation Area

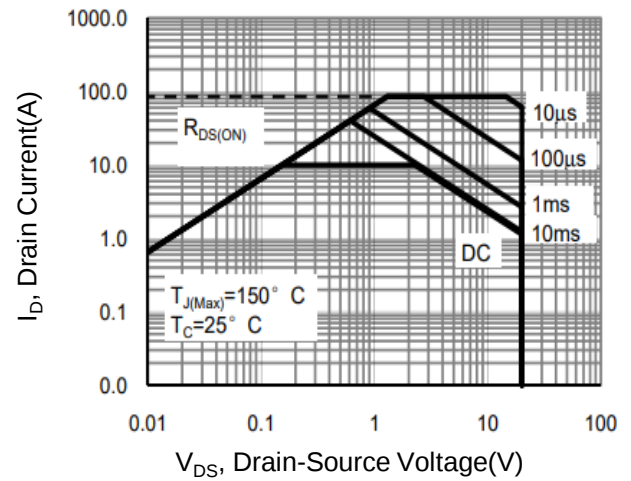
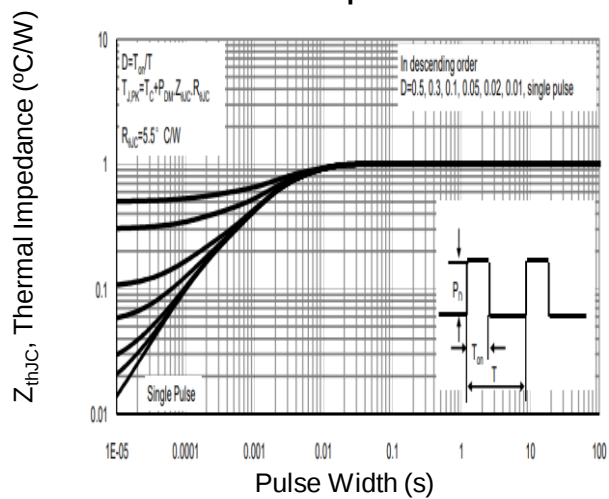
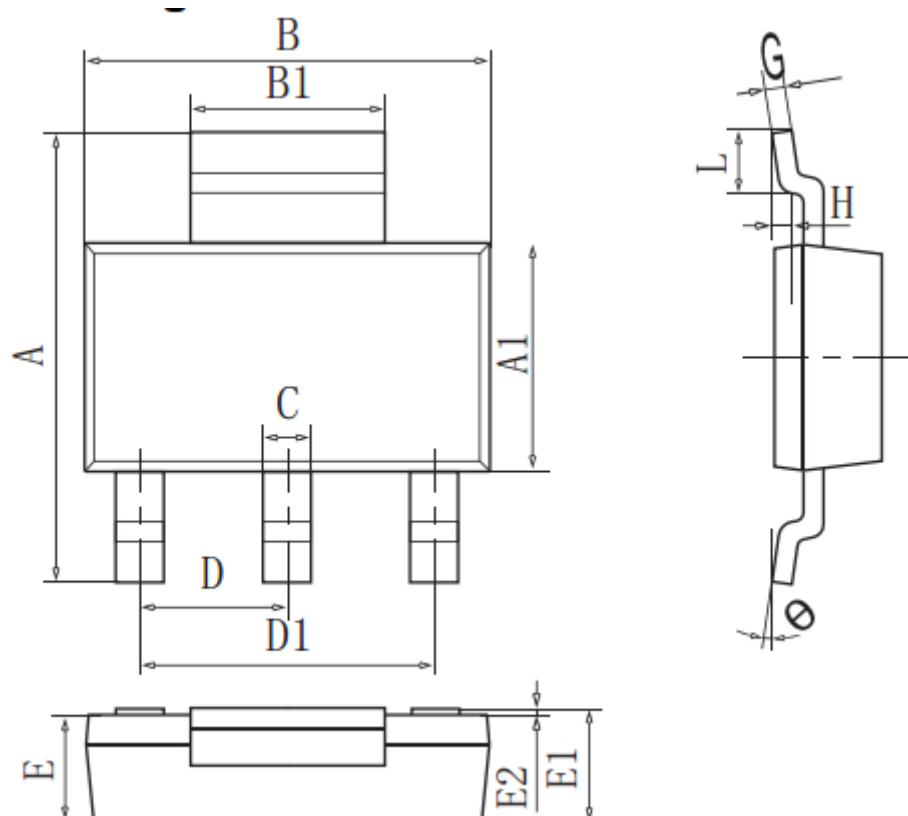


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-223-3L Package Information



DIM	MIN	NOM	MAX
A	6.80	7.00	7.20
A1	3.30	3.50	3.70
B	6.40	6.60	6.80
B1	2.96	3.00	3.10
C	0.66	0.70	0.80
D	2.25	2.30	2.35
D1	4.60REF		
E	1.50	1.60	1.70
E1	1.65REF		
E2	0.02	0.06	0.10
G	0.255	0.305	0.355
H	0.25GAUGR		
L	0.90	-	-
θ	0°	-	10°
All Dimensions in mm			